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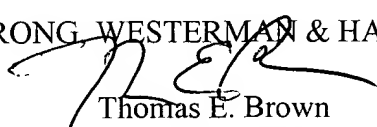
Sir:

Submitted herewith are verified translations of the certified copies of foreign priority documents JP 9-289836 and JP 9-128898 for the above-identified application. These translations are being submitted to perfect the claim for foreign priority.

In the event any fees are due in connection with this paper, please charge our Deposit Account No. 01-2340.

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I, Tadahiko Itoh, a Patent Attorney of Tokyo, Japan having my office at 32nd Floor, Yebisu Garden Place Tower, 20-3 Ebisu 4-Chome, Shibuya-Ku, Tokyo 150-6032, Japan do solemnly and sincerely declare that I am the translator of the attached English translation and certify that the attached English translation is a correct, true and faithful translation of the Japanese Patent Application No. 9-289836 to the best of my knowledge and belief.

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This is to certify that the annexed is a true copy  
of the following application as filed with this office.

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Application Number:       Japanese Patent Application  
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Applicant(s):             FUJITSU LIMITED

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[Title of Document] Specification

[Title of the Invention]

Mounting Method of Semiconductor Device

[Scope of Claim for a Patent]

5 [Claim 1]

A method for mounting a semiconductor chip component on a substrate by pressing so as to weld bumps of a semiconductor component and pads of the substrate and by hardening an adhesive filled  
10 between the semiconductor component and the substrate, said method characterized by:

welding the bumps to pads of the substrate by pressure before said adhesive is hardened and by releasing that pressure welding after the adhesive  
15 is hardened.

[Claim 2]

A method for mounting a semiconductor component on a substrate by moving a head for heating and pressuring, which supports the semiconductor  
20 component, so as to weld bumps of the semiconductor component and bumps on the substrate by pressure and hardening an adhesive filled between the components and the substrate by heat from the head, said method characterized by:

25 moving the head, which is heated to reach temperature at which said adhesive is hardened, so that the bumps press the pads before the adhesive is hardened, and by releasing a pressure welding after the adhesive is hardened.

30 [Claim 3]

A method for mounting a semiconductor component on a substrate by welding by pressure bumps of the semiconductor component to pads on the substrate by moving a head for heating and pressuring, which is  
35 heated to reach temperature at which a thermosetting adhesive is hardened, to weld the semiconductor component to the pads on the substrate by pressuring

the semiconductor component provided on the substrate, and by hardening the thermosetting adhesive filled between the component and the substrate by heat from the head, said method  
5 characterized in that:

a heat conduction delay member for delaying heat conduction is provided so as to intervene between the head and the semiconductor component when the head is pressed and welded to the  
10 semiconductor component and so as to delay the heat conduction from the head to the heat conduction delay member when the head is pressed and welded to the semiconductor component.

[Claim 4]

15 The method is claimed in claim 3, characterized in that the heat conduction delay member is a sheet, is moved so as to move out a portion of the sheet sandwiched between the head and the semiconductor component, position an unused portion of the sheet  
20 to face a bottom surface of the head, and always intervene the unused portion between the head and the semiconductor component.

[Claim 5]

The method as claimed in claim 3, characterized  
25 in that said heat conduction delay member is a polyimide film sheet, a polyester film sheet, or a silicon film sheet.

[0001]

[Technical Field Pertinent to the Invention]

30 The present invention generally relates to a mounting method of a semiconductor device, and more particularly to a method of mounting a semiconductor device on a board in accordance with a COB (Chip On Board) method.

35 [0002]

[Description of Related Art]

Various methods have been proposed as the COB



(Chip On Board) method of mounting a semiconductor device on a board, based on purposes and uses of the semiconductor device. A flip-chip mounting method is one of the methods proposed as the COB method. In  
5 this mounting method, a semiconductor device (a semiconductor chip) is directly mounted on a board without wires connecting the semiconductor device to the board. The flip-chip mounting method is also called a wireless bonding mounting method.

10 [0003]

A description will be given, with reference to Figs. 1A through 1F, of the flip-chip mounting method.

Pads 2, which are electrodes, are formed on a  
15 chip 1 (the semiconductor device) to be mounted on a board 3. Pads 4 which are parts of conductive wiring patterns are formed on the board 3 on which the chip 1 is to be mounted.

First, bumps are formed as shown in Fig. 1A. Referring to Fig. 1A, an end portion of a gold wire  
20 5 is pressed on a pad 2 of the chip 1 and heated by a bonding tool so as to be joined to the pad 2. In this state, the gold wire 5 is then removed. As a result, a tear-drop shaped bump 6 is formed on the  
25 pad 2. On all the pads 2 of the chip 1, tear-drop shaped bumps 6 are formed in the same manner as that describe above.

[0004]

Next, the tear-drop shaped bumps 6 are  
30 flattened as shown in Fig. 1B. Referring to Fig. 1B, the tear-drop shaped bumps 6 are pressed on a flat plate 7 so that only a point end portion of each of the tear-drop shaped bumps 6 is subjected to the plastic deformation. As a result, the tear-drop  
35 shaped bumps 6 are shaped into bumps 6 having substantially the same height.

Conductive paste is then transferred to a

surface of each of the bumps 6 as shown in Figs. 1C and 1D. That is, the end portions of the bumps 6 are immersed in a layer of conductive paste 8 as shown in Fig. 1C and then pulled up therefrom as shown in Fig. 1D. As a result, a drop of the conductive paste 8 is adhered to the end portion of each of the bumps 6. The conductive paste 8 is made, for example, of epoxy resin in which a large amount of silver fillers are distributed. Due to the drop of the conductive paste 8, positive electrical conductivity can be maintained between each of the bumps 6 of the chip 1 and a corresponding one of the pads 4 of the board 3 when the chip 1 is mounted on the board 3.

[0005]

Next, adhesive 9 is applied to or printed on the surface of the board 3 so that the pads 4 are covered with the adhesive 9 as shown in Fig. 1E. A thermosetting insulating adhesive, made of material including epoxy resin as the principal ingredient, is used as the adhesive 9 to be applied to the board 3. In a state where the chip 1 is mounted on the board 3, the space between the chip 1 and the board is filled with the adhesive 9. As a result, the chip 1 and the board 3 are tightly joined to each other. In addition, a connecting portion in which each of the bumps 6 are joined to a corresponding one of the pads 4 is covered with the adhesive 9, so that moisture is prevented from entering the connection portion by the adhesive 9.

[0006]

Finally, the chip 1 is mounted on the board 3 as shown in Fig. 1F. Referring to Fig. 1F, the chip 1 is positioned so that each of the bumps 6 of the chip 1 corresponds to one of the pads 4 of the board 3. A thermopressing head then presses the chip 1 on the board 3, so that each of the bumps 6 is pressed on a corresponding one of the pads 4 of the board 3.

The adhesive 9 and the conductive paste 8 are thus hardened by the heat, so that the chip 1 is completely mounted on the board 3.

[0007]

5 [Problem to be solved by the Invention]

The board on which semiconductor devices are mounted is set and used in electronic equipment, such as a personal computer. Due to the heat generated by the semiconductor devices on the board, the interior of such electronic equipment is at a high temperature. Particularly, in a case where a processor operated at a high frequency is included in the semiconductor device, a large amount of heat is generated. On the other hand, in a case where the electronic equipment is not used, that is, a power supply of the electronic equipment is in an off-state, the interior temperature of the electronic equipment decreases to a room temperature.

[0008]

20 The interior temperature variation of the electronic equipment affects the connecting portion in which each of the semiconductor devices and the board are connected to each other as follows.

As shown in Fig. 2, due to the temperature variation, the adhesive 9 between the semiconductor device 1 (the chip) and the board 3 is thermally expanded and contracted, so that the volume of the adhesive 9 is varies. Of course, thermal expansion and contraction occurs in the board 3, the semiconductor device 1 and the bumps 6. However the rate of expansion (contraction) thereof is less than that of expansion of the adhesive 9. Thus, in a case

where the temperature is increased, the volume of the adhesive 9 is increased and the increase of the volume of the adhesive 9 functions as a force to increase the distance between the board 3 and the semiconductor device. As a result, a contact force

of the bumps 6 to the pads 4 of the board 3 is decreased, so that an electric contact resistance between each of the bumps 6 and a corresponding one of the pads 4 is increased.

5 [0009]

Further, when the temperature is repeatedly increased and decreased, the electrical contact resistance is successively increased and finally a disconnection may occur between the bumps 6 and the  
10 pads 4.

The present invention is to provide a method of mounting a semiconductor device on a board so that even if the volume of adhesive between the semiconductor device and the board is varied by the  
15 variation of temperature, an increase of the electrical contact resistance of the semiconductor device to the board can be prevented.

[0010]

[Means for Solving Problem]

20 To solve the above-mentioned problem, the timing of pressing and releasing is concerned when bumps of a semiconductor device is pressed with heat on pads of a board after the semiconductor device is positioned. That is, in the process of pressing and  
25 heating an adhesive is hardened to maintain the pressure force of the bumps to the pads on a board.

[0011]

The present invention of Claim 1 provides a method for mounting a semiconductor chip component  
30 on a substrate by pressing so as to weld bumps of a semiconductor component and pads of the substrate and by hardening an adhesive filled between the semiconductor component and the substrate, said method characterized by welding the bumps to pads of  
35 the substrate by pressure before said adhesive is hardened and by releasing that pressure welding after the adhesive is hardened.

[0012]

Thereby, the present invention provides a method of mounting a semiconductor device on a board so that even if the volume of an adhesive between  
5 the semiconductor device and the board is varied by the variation of temperature, an increase of the electrical contact resistance of the semiconductor device to the board can be prevented.

In addition, to reduce the time consumption to  
10 mount a semiconductor device on a board is important to cut production cost. Thus, according to the present invention a head for pressuring and heating is preheated by a heater at a temperature sufficient to harden an adhesive so that the time period  
15 required until the adhesive is hardened is reduced. The head is released from pressing the semiconductor device after the adhesive is hardened and pressure force of the bump to the pad is maintained.

[0013]

20 That is, the present invention of Claim 2 provides a method for mounting a semiconductor component on a substrate by moving a head for heating and pressuring, which supports the semiconductor component, so as to weld bumps of the  
25 semiconductor component and bumps on the substrate by pressure and hardening an adhesive filled between the components and the substrate by heat from the head, said method characterized by moving the head, which is heated to reach temperature at which said  
30 adhesive is hardened, so that the bumps press the pads before the adhesive is hardened, and by releasing a pressure welding after the adhesive is hardened.

[0014]

35 According to the present invention, the adhesive can be hardened in a shorter time period. Also, since the bumps are pressed on the pads with a

pressing force of a predetermined value before the adhesive is completely hardened, the bumps can be securely joined to the pads so as to provide a sufficient contact area. Thus, even if the hardened  
5 adhesive is expanded and contracted by the variation of temperature, the electrical contact between the bumps and the pads can be maintained.

[0015]

[Mode for Carrying out the Invention]

10 A description will be given, with reference to Figs. 3 through 5, of a mounting method according to an embodiment of the present invention.

Referring to Fig. 3, a chip 31 (the semiconductor device to be mounted) is supported by  
15 a thermopressing head 30. The chip 31 is mounted on a board 33 by an operation of the thermopressing head 30.

The thermopressing head 30 is movable in directions indicated by arrows in Fig. 3 and  
20 provided with a heater 301 and a vacuum cavity 302. The heater 301 is supplied with an electric current from a power supply. The heater 301 generates an amount of heat sufficient to warm up adhesive 39 (which will be described later) to a temperature  
25 needed to harden the adhesive 39. The vacuum cavity 302 is connected to a vacuum system (not shown) so as to support the chip 31 by a suction force of the vacuum.

[0016]

30 A bump 36 made of gold (Au) is formed on a pad 32 of the chip 31. The bump 36 has a bowl-shaped root portion and an end portion.

An end of a gold wire is pressed on the pad 32 and heated by a bonding tool so as to be joined to  
35 the pad. The gold wire is then removed. As a result, the bump 36 having a tear-drop shape is formed on the chip 31. The point end portion of the tear-drop

shaped bump 36 is flattened. Conductive paste 38 is then transferred to or printed on the surface of the flattened end portion of the bump 36. The conductive paste 38 is made of a thermosetting resin, such as the epoxy resin, in which silver (Ag) fillers are distributed. The conductive paste 38 transferred to the flattened end portion of the bump 36 is preheated so as to be in a semi-hardened state.

[0017]

10       The surface of the chip 1 opposite to the surface on which a circuit is formed is held in position by the vacuum cavity 302, so that the chip 31 is supported by the thermopressing head 30.

15       The board 33 is positioned and fixed on a table 40. A pad 34 which should be electrically connected to the bump 36 is formed on the board 33. The pad 34 is generally made of copper (Cu).

[0018]

20       The adhesive 39 is applied to the surface of the board by using a dispenser or a printing technique. The adhesive 39 is made of thermosetting insulating resin including epoxy resin as the principal ingredient. The adhesive 39 has a heating characteristic by which liquidity of the adhesive is produced by an initial heating stage and then is gradually hardened with increasing temperature.

[0019]

30       Thus, since liquidity of the adhesive 39 applied to the whole surface of the board 33 is temporarily produced when the chip 32 is pressed on the board 33 by the thermopressing head 30, the adhesive 39 is prevented from flowing between the bump 36 of the chip 32 and the pad 34 of the board 33. The adhesive 39 may be applied to the surface of the board 33, except for the pad 34, by using the printing technique.

[0020]

Fig. 4 is a timing chart indicating a time variation of the temperature and pressure in a thermopressing step. In Fig. 4, the axis of the abscissa indicates the time  $t$  and the axis of ordinate indicates the temperature  $T$  and the pressure  $P$ .

In a state where the chip 32 is set in the thermopressing head 30, the thermopressing head 30 start to go down toward the table 40. The chip 32 is pressed on the board 33 by the thermopressing head 30. While the thermopressing head 30 is going down, the contact pressure  $PP$  of the bump 36 of the chip 32 to the pad 34 of the board is gradually increased from a time  $t_0$ .

[0021]

In addition, the temperature  $TT$  of the adhesive 39 is gradually increased from room temperature  $RT$ . The reason is that the thermopressing head 30 is preheated by the heater 301 at a temperature sufficient to harden the adhesive 39.

While the temperature  $TT$  of the adhesive 39 is gradually increased, liquidity of the adhesive 39 is temporarily produced, that is, the viscosity of the adhesive is decreased. Thus, the adhesive 39 applied to the surface of the pad 34 is eliminated by the bump 36 being pressed on the pad 34. As a result, the adhesive 39 will not be present between the bump 36 and the pad 34.

[0022]

While the thermopressing head 30 is moving further down, the contact pressure  $PP$  and the temperature  $TT$  of the adhesive 39 are increased. The thermopressing head 30 stops movement at a time  $t_1$  and is maintained at the position.

At this time ( $t_1$ ), the contact pressure  $PP$  of the bump 36 to the pad 34 is maintained at a value  $PA$  shown in Fig. 5.



[0023]

Fig. 5 shows a relationship between the contact pressure  $P$  and the electrical contact resistance  $R$  between the gold (Au) and the copper (Cu). In a region in which the contact pressure  $P$  is small, the electrical contact resistance is large. This region means that the connection between the gold and the copper is inferior. When the contact pressure  $P$  is increased and reaches a value equal to or greater than  $P_1$ , the electrical contact resistance rapidly decreases. This state means that the connection between the gold and the copper is favorable.

[0024]

The value  $PA$  at which the contact pressure  $PP$  of the bump 36 to the pad 34 should be controlled is set so as to be greater than the value  $P_1$ . For example, it is preferable that the value  $PA$  is set at 30 grams. The value  $PA$  of the contact pressure  $PP$  is a value sufficient to provide plastic deformation to not only the end portion of the bump 36 but also the root portion of the bump 36. In addition, due to the contact pressure  $PP$  at the value  $PA$ , the pad 34 of the board 33 is subjected to plastic deformation by the bump 36.

[0025]

At the time  $t_1$ , the temperature  $TT$  of the adhesive 39 does not reach a hardening temperature  $HT$  at which the adhesive 39 should be hardened. At a time  $t_3$ , the adhesive 39 starts to be heated at the hardening temperature  $HT$ .

Until the time  $t_3$ , the adhesive 39 is gradually hardened. From the time  $t_3$ , the adhesive 39 is heated at the hardening temperature  $HT$  so as to be rapidly hardened. A time needed to completely harden the adhesive 39 depends on ingredients of the adhesive 39 and is, for example, within a range between 15 seconds and 20 seconds.

[0026]

Until the adhesive 39 is completely hardened, the thermopressing head 30 maintains the bump 36 in a state in which it is pressed on the pad 34 with a contact pressure PP of the value PA.

At a time  $t_4$ , after the adhesive 39 is completely hardened, the vacuum cavity 302 of the thermopressing head 30 is returned to atmospheric pressure so that the chip 32 is released from being supported by the thermopressing head 30. The thermopressing head 30 then starts to go up. Since the adhesive 39 is released from being heated by the thermopressing head 30, the temperature of the adhesive 39 is gradually decreased to the room temperature RT.

[0027]

With decreasing of the temperature, the volume of the adhesive 39 is decreased, that is, the adhesive 39 is contracted. Thus, it is expected that the contact pressure is temporarily decreased immediately after the head 30 goes up and is separated from the chip 31. However, due to the contraction of the adhesive based on the decreasing temperature, a tension force is generated between the chip 31 and the board 33. As a result, the pressure force of the bump 36 to the pad 34 returns to and can be maintained at the initial value PA.

[0028]

Thus, in a state where the chip 31 is used inside electronic equipment, even if the adhesive 39 is expanded and contracted based on the variation of the temperature, a decrease of the contact pressure of the bump 36 to the pad 34 can be limited to a minimum value. As a result, the reliability of the electrical connection of the chip 1 with the board 33 can be maintained.

[0029]

The thermopressing head 30 from which the chip 32 has been separated is maintained at the hardening temperature of the adhesive. In the manufacturing process, the next chip is then supported on the thermopressing head 30 by the vacuum suction force.  
[MODIFICATIONS OF THE EMBODIMENT]

In the above embodiment, the conductive paste 38 covering the surface of the bump 36 is made of resin in which silver fillers are distributed.  
However, the conductive paste 38 may be made of anisotropic conductive adhesive in which capsules are distributed, each of the capsules being formed by covering silver articles with resin. In this case, the cover of each of the capsules is broken when the bump is pressed on the pad. The silver articles being positioned between the bump and the pad.  
[0030]

In addition, the electrical connection between the bump 36 and the pad mainly depends on the direct contact of the bump 36 with the pad. The conductive paste 38 is additionally used for the electrical connection between the bump 36 and the pad. The conductive paste 38 is not necessarily needed.

The bump 38 may have a shape (e.g., a cylindrical shape) other than a shape having the bowl-shaped root portion and the end portion as described above.  
[0031]

The adhesive 39 may be heated by a heater provided near the table, as a substitute for the heater 301 mounted in the thermopressing head.

The adhesive 39 is previously applied to the board 33. After the bump 36 is pressed on the pad, the adhesive 39 may be put into the space between the chip and the board. However, it is preferable that the adhesive 39 is previously applied to the board 33 before the bump 39 is pressed on the pad as

described in the above embodiment.

[0032]

A description will now be given of the mounting method of the semiconductor device according to  
5 another embodiment of the present invention.

In this embodiment, a chip mounting machine as shown in Fig. 6 is used to mount a chip on a board. The chip mounting machine 50 has a head 30A, raising and lowering mechanism 52, a table 40, transferring  
10 mechanism 53 and a head supporting mechanism 54. The raising and lowering mechanism 52 is mounted on a gate-shaped block 51 and causes the head 30A to reciprocate up and down. The head supporting mechanism 54 supports the head 30A.

15 [0033]

A heater 61 and a thermocouple 62 are mounted in a head body 61 of the head 30A. The head 30A is heated at 170°C which is the hardening temperature of the adhesive 39.

20 The transferring mechanism 53 has reel supporting blocks 70 and 71 installed at both sides of the gate-shaped block 51, reels 72 and 73 rotatably supported by the reel supporting blocks 70 and 71, motors 74 and 75 rotating the reels 73 and  
25 74, and a polyimide film sheet 76. The polyimide film sheet 76 is wound on the reels 72 and 73 from both sides thereof so as to cross the gate-shaped block 51. A stainless steel plate 80 which is used as a jig is transferred by a conveyer and set on the  
30 table 40A. The polyimide film sheet 76 is located at a position (H1) slightly higher than the stainless steel plate 80 set on the table 40A. The polyimide film sheet 76 is transferred in a direction A by rotation of each of the reels 72 and 73 respectively  
35 driven by the motors 74 and 75.

[0034]

The polyimide film sheet 76 has a low thermal

conductivity, such as 12°C/cm. The thickness of the polyimide film sheet 76 is 25 m. A heater 90 is mounted in the table 40A, so that the table 40A is heated at 80°C.

5           The raising and lowering mechanism 52 a guide 55 of a head supporting mechanism 54 to go up and down (vertically reciprocate).  
[0035]

10           A description will now be given of the chip mounting method using the chip mounting machine 50 having the structure as described above.

          First, the chip 10 is provisionally mounted on a flexible printed circuit board 81 which is fixed on the stainless steel plate 80, using a chip  
15           provisional mounting machine (not shown). As a result, a semi-finished product 90 in which the chip 10 is provisionally mounted is formed. Next, the semi-finished product 90 is transferred to the chip mounting machine 50 by the conveyer and set therein.  
20           The head 30A presses the chip 10 on the flexible printed circuit board 81, with heat, so that the chip 10 is completely mounted on the flexible printed circuit board 81.

[0036]

25           Fig. 6 shows a state in which the semi-finished product 90 transferred into the chip mounting machine 50 is positioned and set on the table 40A. The polyimide film sheet 76 is slightly over the chip 10.

30           After it is recognized that the semi-finished product 90 is positioned and set on the table 40A, the raising and lowering mechanism 52 is operated so that the head 30A moves downwardly. As enlarged and shown in Fig. 7, the head 30A presses the chip 10 on  
35           the flexible circuit board 81 with application of heat. Between the head 30A and the chip 10, the polyimide film sheet 76 is set. After a

predetermined time has elapsed, the head 30A is caused to move upwardly and separate from the chip 10.

[0037]

5       When the raise and fall mechanism 52 is operated so that the head supporting mechanism 54 moves downwardly and the head 30A is brought into contact with the chip 10, a spring 56 starts to be compressed. After this, the pressure of the head 30A  
10   to the chip 10 is increased by increasing the amount of compression of the spring 56. The raising and lowering mechanism 52 is operated until the amount of compression of the spring 56 reaches a predetermined value. An initial amount of  
15   compression of the spring 56 is adjusted by a screw 57.

[0038]

      The pressing characteristic of the head 30A pressing the chip 10 is indicated by a line I in Fig.  
20   8. That is, the pressure of the head 30A to the chip 10 is gradually increased starting from a time  $t_{10}$  as indicated by a line Ia and reaches a value  $PAa$  at a time  $t_{12}$ . After this, the pressure is maintained at the value  $PAa$  as indicated by a line Ib and is  
25   gradually decreased starting from a time  $t_{14}$  as indicated by a line Ic. The time  $t_{14}$  is a time at which a time period  $T_1$  that is needed to completely harden the adhesive 39 elapses from a time  $t_{13}$  at which the temperature of the adhesive 39 reaches the  
30   hardening temperature of  $170^{\circ}\text{C}$ .

[0039]

      In addition, starting from a time at which the head 30A is brought into contact with the chip 10, the adhesive 39 is heated via the chip 10 until the  
35   temperature of the adhesive 39 reaches the hardening temperature of  $170^{\circ}\text{C}$ . The temperature of the adhesive 39 varies as indicated by a line II in Fig.

8.

If the polyimide film sheet 76 is not set between the head 30A and the chip 10 so that the head 30A is in direct contact with the chip 10, the temperature of the adhesive 39 is rapidly increased as indicated by a line I Ia in Fig. 8. A time period T2 between the time  $t_{10}$  at which the head 30A is brought into contact with the chip 10 and a time  $t_{11}$  at which the temperature of the adhesive 39 reaches the hardening temperature of 170°C is relatively short. As a result, the time  $t_{12}$  at which the pressure of the head 30A to the chip 10 reaches the predetermined value P Aa is after the time  $t_{11}$ . That is, before the pressure of the head 30A to the chip 10 reaches the predetermined value P Aa, the adhesive starts to be hardened. Thus, some of the bumps 36 may be incompletely joined to the pads.

[0040]

On the other hand, according to the above method of the present invention, since the polyimide film sheet 76 is set between the head 30A and the chip 10, the heat is transmitted through the polyimide film sheet 76 having a low thermal conductivity to the adhesive 39. As a result, the temperature of the adhesive 39 is increased, starting from the time  $t_{10}$  at which the head 30A starts to press the chip 10, to the hardening temperature of 170°C as indicated by a line I Ib. The line I Ib is more gently sloping than the line I Ia. A time period T3 between the time  $t_{10}$  at which the head 30A starts to press the chip 10 and the time  $t_{13}$  at which the temperature of the adhesive 39 reaches the hardening temperature of 170°C is greater than the time period T2 described above by T4.

[0041]

Thus, the pressure of the head 30A to the chip

10 reaches the predetermined value PAa at the time  
t<sub>12</sub>, before the time t<sub>13</sub>. That is, before the  
adhesive 30 starts to be hardened, the pressure of  
the head 30A to the chip 10 reaches the  
5 predetermined value PAa. After the pressure reaches  
the predetermined value, the adhesive 39 starts to  
harden. As a result, the bump 36 is appropriately  
pressed on the pad so as to be securely joined to  
the pad. Thus, the chip 10 can be mounted on the  
10 board with a high reliability.  
[0042]

In addition, in Fig. 8, a line IIc indicates an  
increasing characteristic of the temperature of the  
adhesive 39 when the semi-finished product 90 is set  
15 on and heated by the table 40A.

Since the polyimide film sheet 76 has a heat  
resistance property, the polyimide film sheet 76  
does not adhere to the head 30A and chip 10. The  
polyimide film sheet 76 is flexible, so that the  
20 surface of the chip 10 is not damaged.  
[0043]

After the head 10A moves upwardly and is  
separated from the chip 10, the motors 73 and 74 are  
driven so that the polyimide film sheet 76 is moved  
25 by one step. As a result, a part of the polyimide  
film sheet 76 which was set between the head 30A and  
the chip 10 is moved to the outside of the  
gate-shaped block 51 and a new part of the polyimide  
film sheet 76 which has not yet been used is fed  
30 into a space in the gate-shaped block 51. The new  
part of the polyimide film sheet 76 is used for the  
next semi-finished product 90 so as to be set  
between the head 30A and the chip 10.  
[0044]

35 A polyester film sheet or a silicon film sheet  
may be substituted for the polyimide film sheet 76.

Instead of setting material having a low



thermal conductivity, such as the polyimide film sheet 76, between the head 30A and the chip 10, the head 30A may be temporarily cooled immediately before the head 30A is brought into contact with the  
5 chip 10.  
[0045]

If the heater in the head 30A is turned on after the head 30 presses the chip 10, the adhesive 39 can start to be hardened after the pressure of  
10 the head 30A to the chip 10 reaches the predetermined value PAa without the polyimide film sheet 76. However, according to this method, a time period required for mounting the chip is increased, so that production deteriorates. From a viewpoint of  
15 production, the method according to the above embodiment of the present invention is preferable.  
[0046]

[Advantage of the Invention]

According to the present invention, since the  
20 bumps are pressed on the pads with a pressing force of a predetermined value before the adhesive is completely hardened, the bumps can be securely joined to the pads so as to provide a sufficient contact area. Thus, even if the hardened adhesive is  
25 expanded and contracted by the variation of temperature, the electrical contact between the bumps and the pads can be maintained.  
[0047]

Further, since the thermopressing head is  
30 preheated at a temperature at which the adhesive can be hardened, the pressure of the bumps against the pads by the head reaches a predetermined value before a temperature of the adhesive reaches temperature at which the adhesive is hardened, and  
35 the pressure is released after the adhesive is completely hardened, the adhesive is heated much faster and thus the time required for mounting is

shortened.

[0048]

A method of mounting a semiconductor device having bumps on a board having pads so that each of  
5 said bumps is joined to a corresponding one of said pads, an adhesive to be hardened by heat being provided between said semiconductor device and said board, said method comprising the steps of:  
10 providing a member between said semiconductor device and said board, said member having a thermal characteristic of delaying transmission of heat; causing a head heated at a temperature at which said adhesive is hardened to press said semiconductor device against said board via said member so that  
15 each of said bumps is pressed against a corresponding one of said pads, wherein the transmission of the heat from said head to said adhesive is delayed by said member so that pressure of said bumps against said pads reaches a  
20 predetermined value before a temperature of said adhesive to which heat is supplied from said head reaches a temperature at which said adhesive is hardened; and releasing said head from pressing said semiconductor device after said adhesive is  
25 completely hardened. Thus, the present invention provides a mounting method with the time reduction and a high reliability.

[Brief Description of Drawings]

[FIG.1]

30 Diagrams illustrating a procedure of mounting a semiconductor device on a board.

[FIG.2]

Cross sectional view showing a connecting portion in which the semiconductor device and the  
35 board are connected to each other.

[FIG.3]

Diagram illustrating a relationship between the

board and the semiconductor device supported by a head used in a thermopressing step.

[FIG.4]

5 Timing chart illustrating a variation of contact pressure of a bump to a pad and a variation of adhering temperature.

[FIG.5]

10 Characteristic diagram illustrating a variation of contact resistance to a variation of contact pressure between gold (Au) and copper (Cu).

[FIG.6]

Diagram illustrating an example of a chip mounting machine.

[FIG.7]

15 Diagram illustrating a polyimide film set between the head and the chip in the thermopressing step.

[FIG.8]

20 Diagram illustrating a variation of a pressing force of the head to the chip and a variation of the temperature of the adhesive.

[Description of Reference Numerals]

- |    |            |                                 |
|----|------------|---------------------------------|
|    | 1 and 31   | a semiconductor device (a chip) |
|    | 2 and 32   | pads on a semiconductor device  |
| 25 | 4 and 34   | pads on a board                 |
|    | 6 and 36   | bumps                           |
|    | 8 and 38   | conductive paste                |
|    | 9 and 39   | an adhesive                     |
|    | 30 and 30A | a thermopressing head           |
| 30 | 301        | a heater                        |
|    | 40         | a table                         |
|    | HT         | hardening temperature           |
|    | RT         | room temperature                |
|    | PA         | pressure of a bump to a pad     |
| 35 | 50         | a chip mounting machine         |
|    | 53         | transferring mechanism          |
|    | 76         | polyimide film sheet            |

[Title of Document] Abstract

[Abstract]

[Problem]

5 It is a general object of the present invention  
related to a method of mounting a semiconductor  
device having bumps on a board having pads to  
prevent an increase of the electrical contact  
resistance of the semiconductor device to the board  
from an increase of the volume of an adhesive  
10 between the semiconductor device and the board by  
the variation of temperature.

[Solving Means]

A method of mounting a semiconductor device  
having bumps on a board having pads so that each of  
15 the bumps is joined to a corresponding one of the  
pads is provided. Adhesive to be hardened by heat is  
provided between the semiconductor device and the  
board. The method includes the steps of pressing the  
bumps of the semiconductor device on the pads of the  
20 board, and heating a portion in which each of the  
bumps and a corresponding one of the pads are in  
contact with each other. A pressure of the bumps to  
the pads reaches a predetermined value before a  
temperature of the adhesive to which heat is  
25 supplied in the above step reaches a temperature at  
which the adhesive is hardened.

[Selected Drawing] FIG. 4

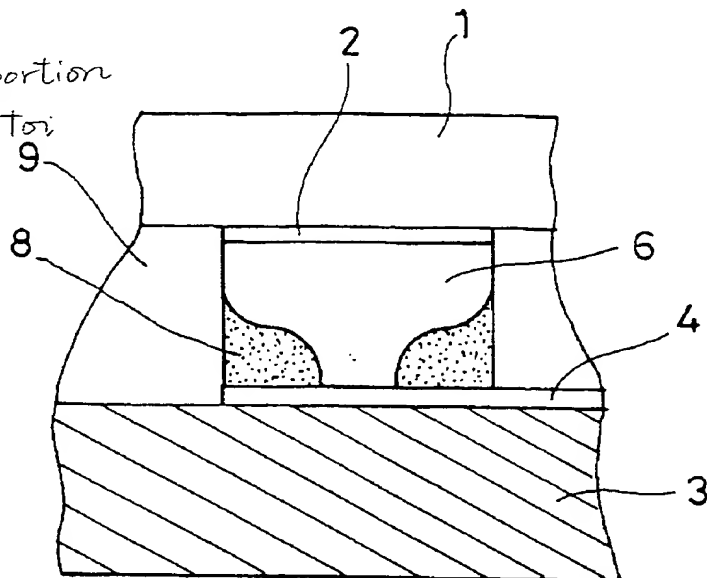


【図2】

FIG. 2

半導体部品を基板に実装した状態の断面図

A Cross Sectional View  
Showing a connecting portion  
in which the Semiconductor  
device and the board  
Are Connected to each  
other.

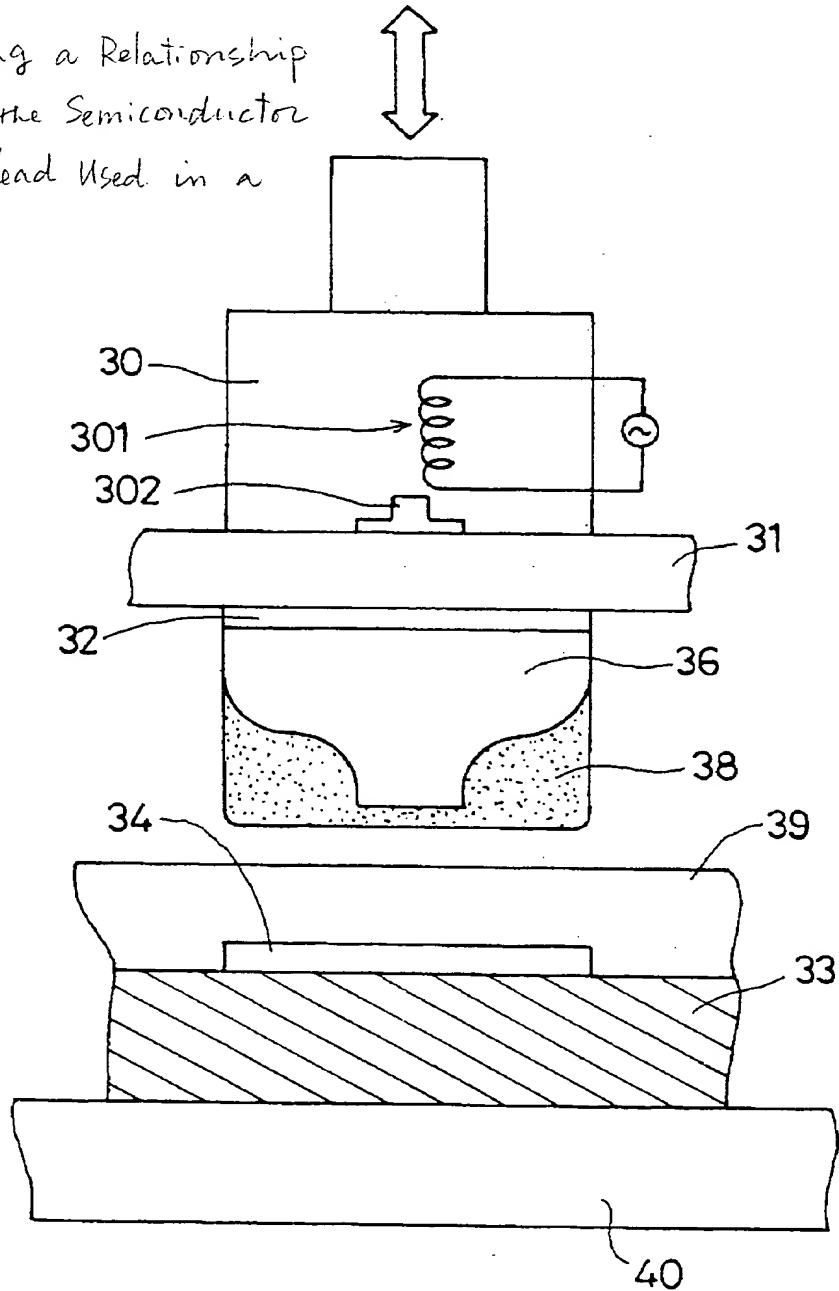


~~【図 3】~~

FIG. 3

~~本発明の実施例を説明するための図面であり、  
加熱・加圧工程におけるヘッドに支持された半  
導体部品と基板との関係を示す図~~

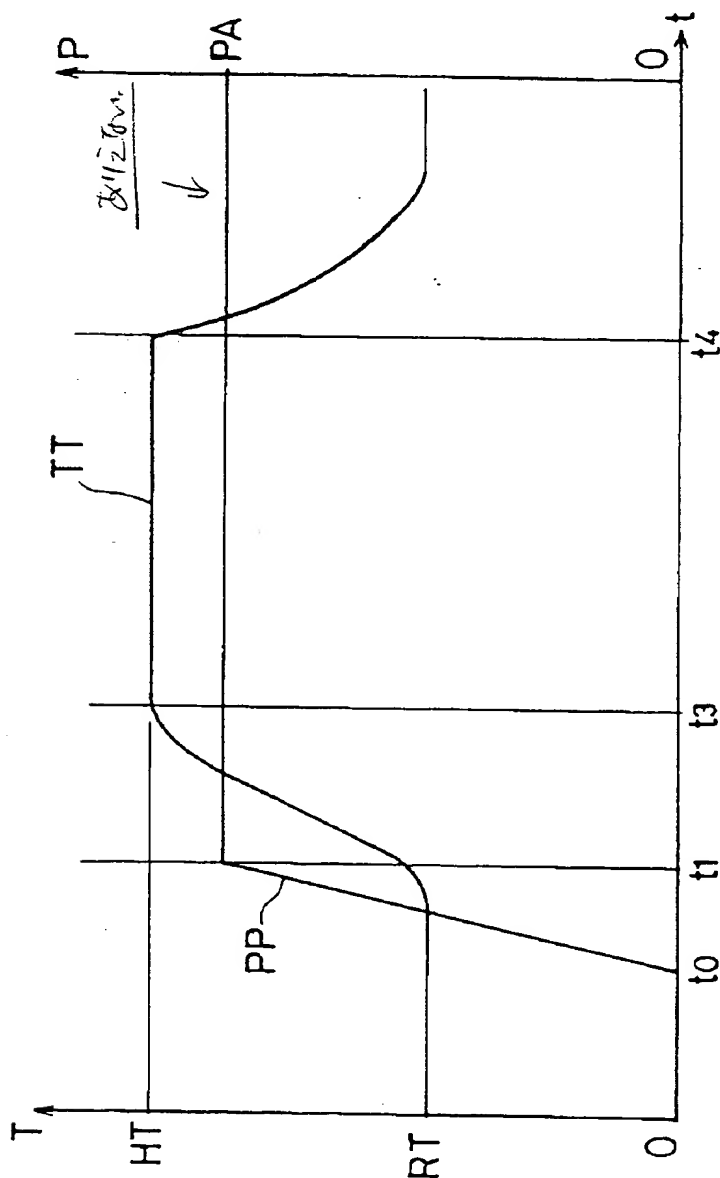
A Diagram Illustrating a Relationship  
Between the Board and the Semiconductor  
Device Supported by a Head Used in a  
Thermopressing Step.



世

A Timing Chart Illustrating a Variation of Contact Pressure of a Bump to a Pad and a Variation of Adhering temperature

本発明の実施例を説明するための図面であり、加熱・加圧工程におけるハンダとバンドとの圧接  
力及び接着温度の変化を示すタイムチャート



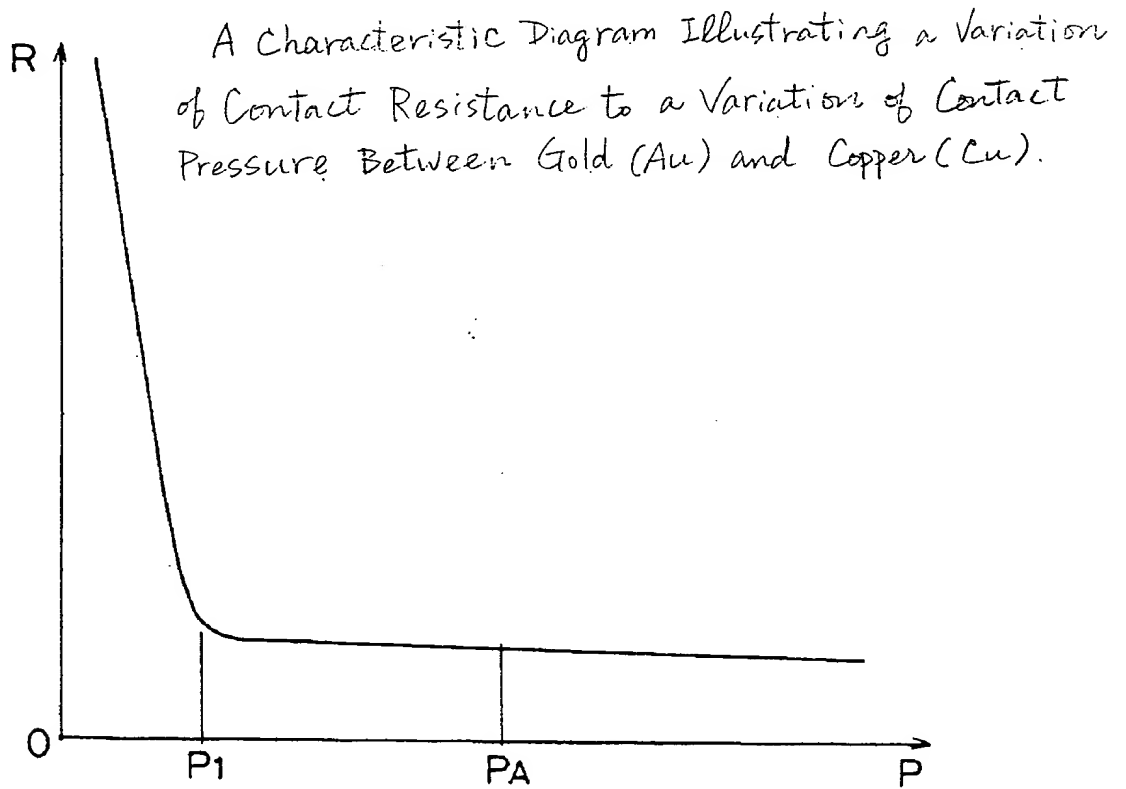


~~図 5~~

FIG. 5

~~本発明の実施例を説明するものであり、金(Au)と銅(Cu)との圧接力と両者間の抵抗との変化を示す特性図~~

↓

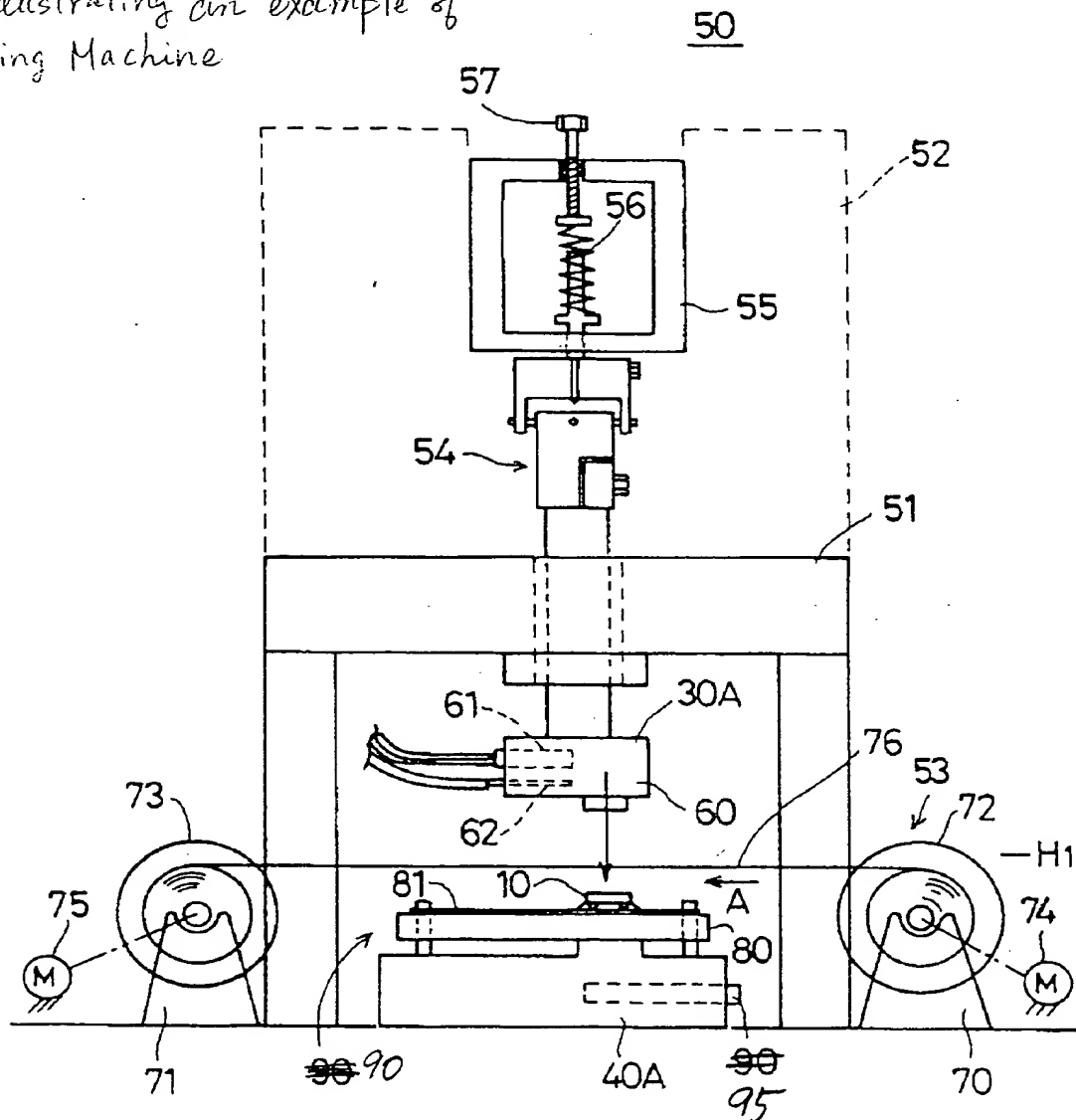


~~【図6】~~

FIG. 6

~~本発明の半導体部品の実装方法の別の実施例  
に使用されるチップ実装装置を示す図~~

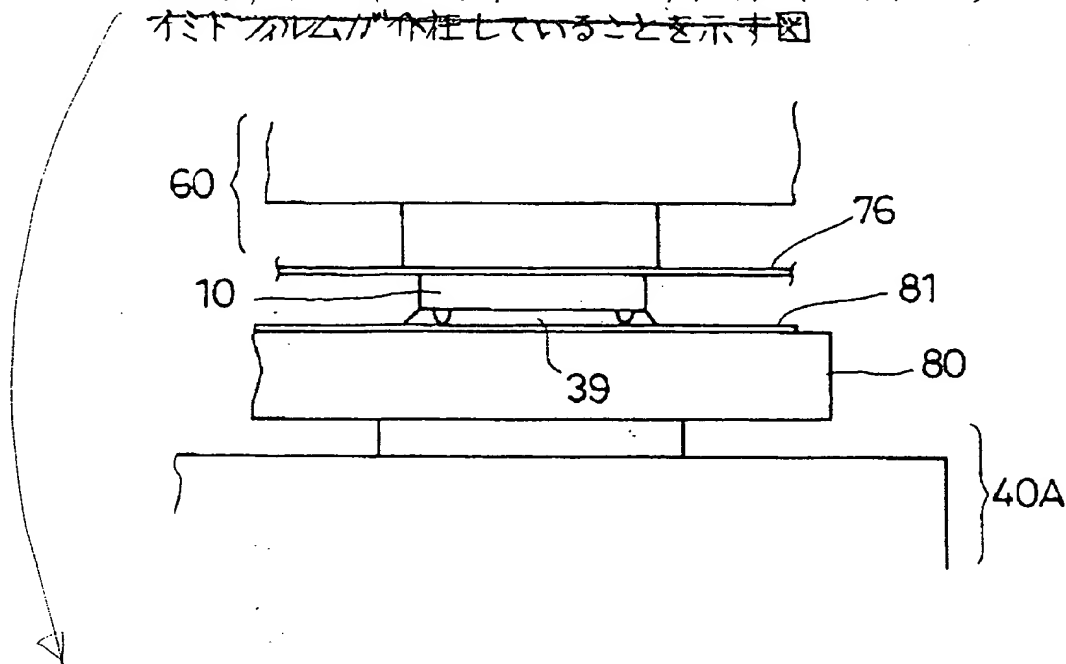
A Diagram Illustrating an example of  
a Chip Mounting Machine



【図7】

FIG. 7

加熱・加圧工程におけるヘッドとチップの間に帯状ポリイミドフィルムが介在していることを示す図

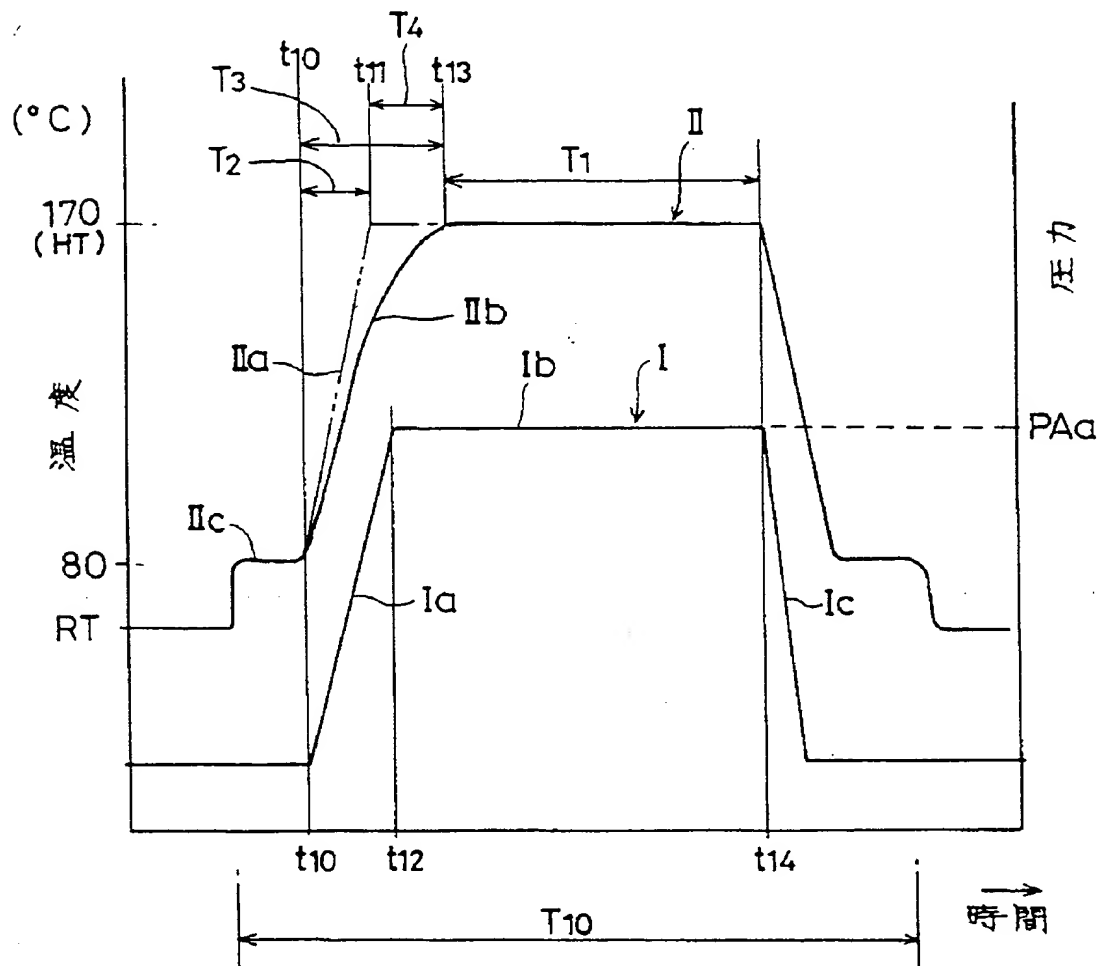


A Diagram Illustrating a Polyimide Film Set  
Between the Head and the Chip in the Thermopressing Step.

【図8】

FIG. 8

加熱・加圧工程におけるヘッドのチップへの押圧力と接着剤の温度の変化を併せて示す図



A Diagram Illustrating a Variation of a Pressing Force of the Head to the Chip and a Variation of the Temperature of the Adhesive